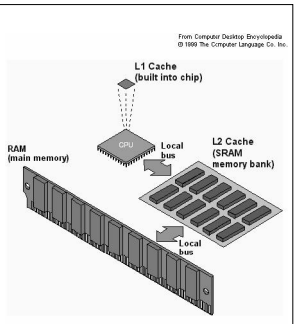
Luento 4

Tietokoneen rakenne

Internal Memory, Cache



Stallings: Ch 4, Ch 5

- Key Characteristics
- Locality
- Cache
- Main Memory

Key Characterics of Memories / Storage

Location	**Performance**
Processor	Access time
Internal (main)	Cycle time
External (secondary)	Transfer rate
Capacity	**Physical Type**
Word size	Semiconductor
Number of words	Magnetic
Unit of Transfer	Optical
Word	Magneto-Optical
Block	**Physical Characteristics**
Access Method	Volatile/nonvolatile
Sequential	Erasable/nonerasable
Direct	**Organization**
Random	
Associative	

(Sta06 Table 4.1)

Goals

- **I want my memory lightning fast**
- **I want my memory to be gigantic in size**

- **Register access viewpoint**
  - data access as fast as HW register
  - data size as large as memory

cache

HW solution

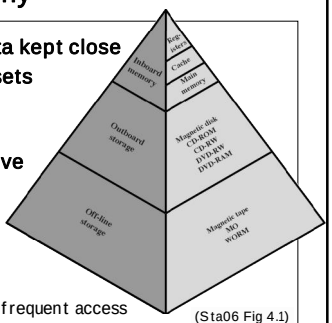
- **Memory access viewpoint**
  - data access as fast as memory
  - data size as large as disk

virtual memory

HW help for SW solution

Memory Hierarchy

- **Most often needed data kept close**
- **Access to small data sets can be made fast**
  - simpler circuits
- **Faster ~ more expensive**
- **Large can be bigger and cheaper (per B)**



up: smaller, faster, more expensive, more frequent access

down: bigger, slower, less expensive, less frequent access

(Sta06 Fig 4.1)

Principle of locality (paikallisuus)

- **In any given time period, memory references occur only to a small subset of the whole address space**

= The reason why memory hierarchies work

Prob (small data set) = 99% "Cost" (small data set) = 2 µs

Prob (the rest) = 1% "Cost" (the rest) = 20 µs

Aver cost = 99% * 2 µs + 1% * 20 µs = 2.2 µs

- **Average cost is close to the cost of small data set**
- **How to determine data for that small set?**
- **How to keep track of it?**

Sta06 Fig 4.2

Principle of locality

- **In any given time period**
  - memory references occur only to a small subset of the whole address space
- **Temporal locality** (ajallinen)
  - it is likely that a data item referenced a short time ago will be referenced again soon
- **Spatial locality** (alueellinen)
  - it is likely that a data items close to the one referenced a short time ago will be referenced soon

MEM: 345 233 71 8 305 63 91 2

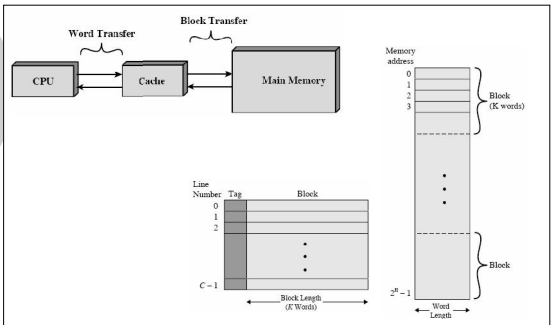
Tietokoneen rakenne

Cache

Cache Memory (välimuisti)

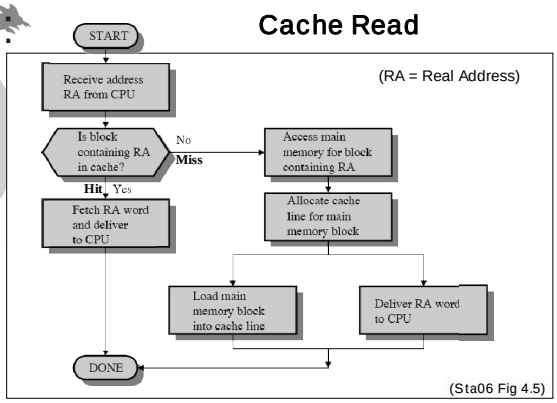
- **How to access main memory as fast as registers?**
- **Locality ž Use (CPU) cache!**
  - Keep most probably referenced data in fast cache close to processor, and rest in memory
  - Most of data accesses only to cache
    - hit ratio 0.9-0.99
  - Much smaller than main memory
  - (much) more expensive (per byte) than memory

Cache



(Sta06 Fig 4.3, 4.4)

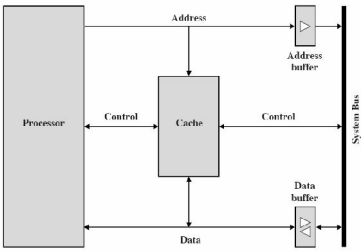
Cache Read



(RA = Real Address)

(Sta06 Fig 4.5)

Cache Organization



(Sta06 Fig 4.6)

Cache Design

Cache Size	**Write Policy**
Mapping Function	Write through
Direct	Write back
Associative	Write once
Set Associative	**Line Size**
Replacement Algorithm	**Number of caches**
Least recently used (LRU)	Single or two level
First in first out (FIFO)	Unified or split
Least frequently used (LFU)	
Random	

- **Size**
  - Many blocks help for temporal locality
  - Large blocks help for spatial locality
  - Multi-level cache

(Sta06 Table 4.2)

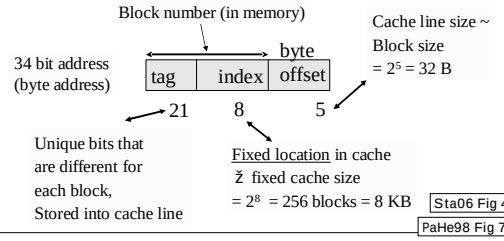
Mapping

- **Which block contains the memory location?**
- **Is the block in cache?**
- **Where is it located?**

- **Solutions**
  - direct mapping (suora kuvaus)
  - fully associative mapping (joukkoassosiatiivinen)
  - set associative mapping (täysin assosiatiivinen)

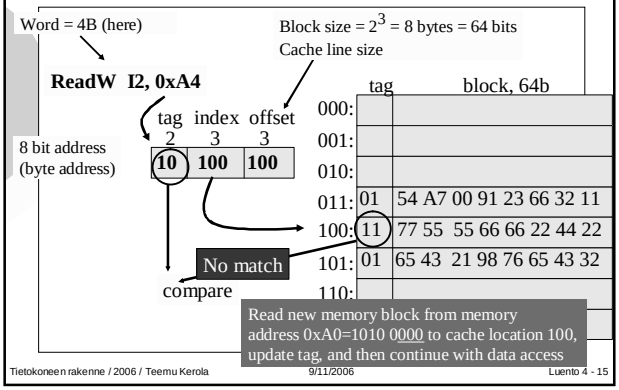
Direct Mapping (4)

- **Each block has only one possible location (line) in cache**
  - determined by index field bits
- **Several blocks may map into same cache line**
  - identified with tag field bits

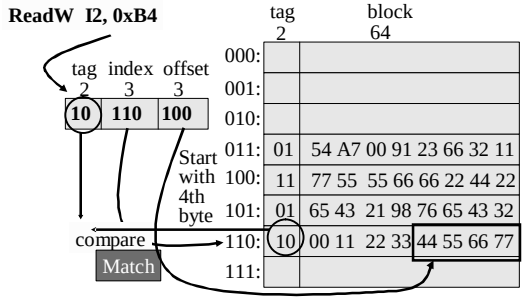


Sta06 Fig 4.7
PaHe98 Fig 7.10

Direct Mapping Example (5)

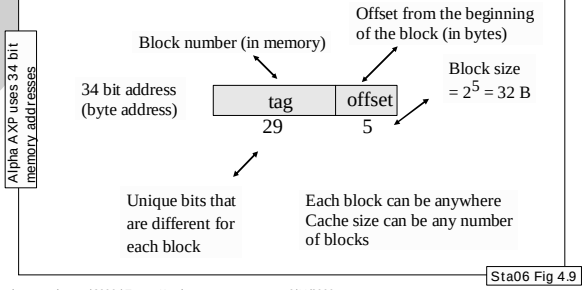


Direct Mapping Example 2 (5)



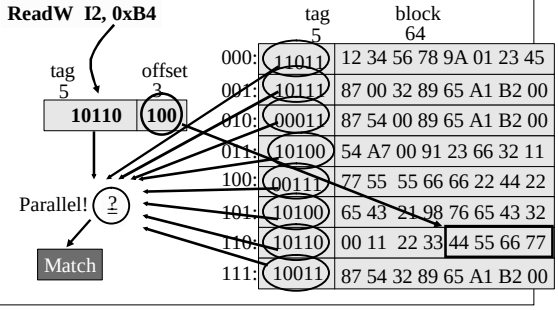
Fully Associative Mapping (6)

- **Each block can be in any cache line**
  - tag must be complete block number



Sta06 Fig 4.9

Fully Associative Example (4)



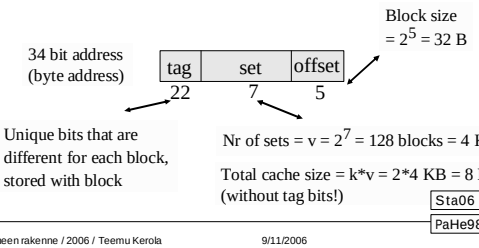
Fully Associative Mapping

- **Lots of circuits**
  - tag fields are long - wasted space?
  - each cache line tag must be compared parallelly with the memory address tag
    - lots of wires, comparison circuits
    - large surface area on chip
- **Final comparison "or" has large gate delay**
  - did any of these 64 comparisons match?
    - $\log_2(64) = 6$ levels of binary OR-gates
  - how about 262144 comparisons?
    - 18 levels?

ð Can use it only for small caches

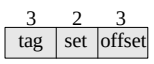
Set Associative Mapping

- **With set size k=2, each cache entry contain 2 blocks**
  - Use set (set index) field to find the cache entry
  - Use tag to determine if the block belongs to the set
  - Use offset to find the proper byte in the block



2-way Set Associative Cache

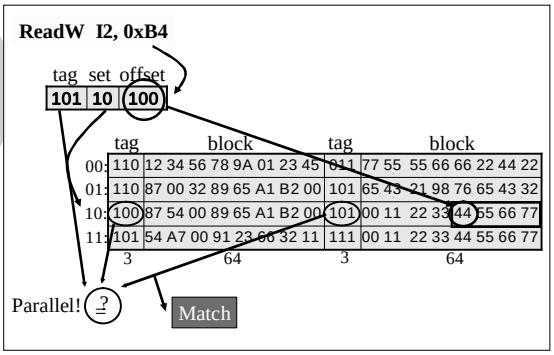
- **k=2 g Two blocks in each set (= in one cache entry)**
- **4 sets g 2 bits for set index**
- **2 words in a block = 8 Bytes g 3 bits for byte offset**
- **3 bits for tag**



8 bit address
(byte address)

	tag	block	tag	block
00:	110	12 34 56 78 9A 01 23 45	011	77 55 55 66 66 22 44 22
01:	110	87 00 32 89 65 A1 B2 00	101	65 43 21 98 76 65 43 32
10:	100	87 54 00 89 65 A1 B2 00	101	00 11 22 33 44 55 66 77
11:	101	54 A7 00 91 23 66 32 11	111	00 11 22 33 44 55 66 77
	3	64	3	64

2-way Set Assoc. Cache Example (5)



Set Associative Mapping

- **Set associative cache with set size k=2 = 2-way cache (common)**
- **Degree of associativity = nbr of blocks in a set = v**
  - Large degree of associativity?
    - More data items in one set
    - Less "collisions" within set
    - Final comparison (matching tags?) gate delay?
  - Maximum (nr of cache lines)
    ð fully associative mapping
  - Minimum (1)
    ð direct mapping

Cache Replacement Algorithm

- **Which cache block to replace to make room for new block from memory?**
- **Direct mapping: trivial**
- **First-In-First-Out (FIFO)?**
- **Least-Frequently-Used (LFU)?**
- **Random?**
- **Which one is best / possible?**
  - Chip area?
  - Fast? Easy to implement?

Cache Write Policy – memory writes?

- **Write through** (läpikirjoittava)
  - Each write goes always to cache and memory
  - Each write is a cache miss!
- **Write back** (lopuksi/takaisin kirjoittava)
  - Each write goes only to cache
  - Write cache block back to memory only when it is replaced in cache
  - Memory may have stale (old) data
  - cache coherence problem (yhdenmukaisuus, yhtäpitävyys)
- **Write once** ("vain kerran kirjoittava?)
  - Write-invalidate Snoopy-cache coherence protocol for multiprocessors
  - Write invalidates data in other caches
  - Write to memory at replacement time, or when some other cache needs it (has read/write miss)

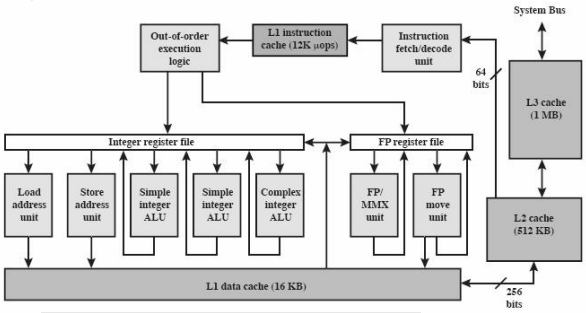
Cache Line Size

- **How big cache line?**
- **Optimise for temporal or spatial locality?**
  - bigger cache line ð better for spatial locality
  - more cache lines ð better for temporal locality
- **Best size varies with program or program phase?**
- **Best size different with code and data?**
- **2-8 words?**
  - word = 1 float??

Types and Number of Caches

- **Same cache for data and code, or not?**
  - Data references and code references behave differently
- **Unified vs. split cache** (yhdistetty/erilliset)
  - split cache: can optimise structure separately for data and code
- **One cache too large for best results**
- **Multiple levels of caches**
  - L1 on same chip as CPU
  - L2 on same package or chip as CPU
    - older systems: same board
  - L3 on same board as CPU

Example: Pentium 4 Block Diagram



L1: split, 4-way set-associative, line size 64 B
L2, L3: unified, 8-way set-associative, line size 128 B

(Sta06 Fig 4.13)

Tietokoneen rakenne

Main Memory

Main Memory Types

Memory Type	Category	Erasure	Write Mechanism	Volatility
Random-access memory (RAM)	Read-write memory	Electrically, byte-level	Electrically	Volatile
Read-only memory (ROM)	Read-only memory	Not possible	Masks	Nonvolatile
Programmable ROM (PROM)			Electrically	
Erasable PROM (EPROM)	Read-mostly memory	UV light, chip-level		
Electrically Erasable PROM (EEPROM)		Electrically, byte-level		
Flash memory		Electrically, block-level		

(Sta06 Table 5.1)

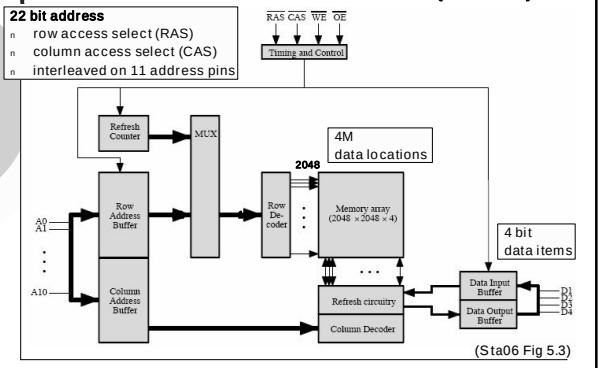
- **Random access semiconductor memory**
  - Direct access to each memory cell
  - Access time same for all cells

RAM

- **Dynamic RAM, DRAM**
  - Periodic refreshing required
  - Refresh required after read
  - Simpler, slower, denser, bigger (bytes per chip)
  - Access time ~ 60 ns
  - Main memory? (early systems)
- **Static RAM, SRAM**
  - No periodic refreshing needed
  - Data remains until power is lost
  - More complex (more chip area/byte), faster, smaller
  - Access time ~ 2-5 ns
  - Level 2 cache?

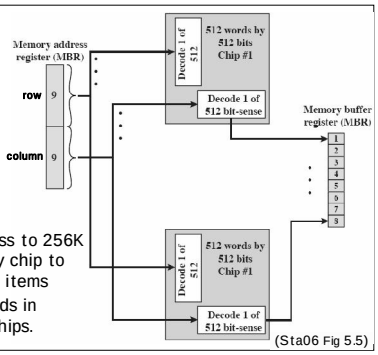
DRAM Access, 16 Mb DRAM (4M x 4)

22 bit address
- row access select (RAS)
- column access select (CAS)
- interleaved on 11 address pins



(Sta06 Fig 5.3)

256-KB DRAM Memory Organization



- Simultaneous access to 256K 8-bit word memory chip to access larger data items
- Access 64-bit words in parallel? Need 8 chips.

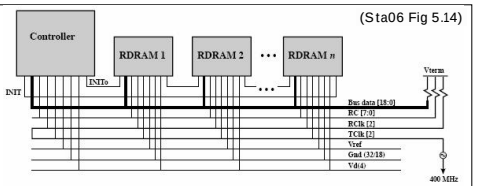
(Sta06 Fig 5.5)

SDRAM (Synchronous DRAM)

- **CPU clock synchronizes also the bus**
  - Runs on higher clock speeds than ordinary DRAM
  - CPU knows how long it takes to make a reference, can do other work while waiting
- **16 bits in parallel**
  - Access 4 DRAMs (4 bits each) in parallel
  - Access time ~ 18 ns, transfer rate ~ 1.3 GB/s
- **DDR SDRAM, double data rate**
  - Current main memory technology
  - Supports transfers both on rising and falling edge of the clock cycle
  - Consumes less power
  - Access time ~ 12 ns, transfer rate ~ 3.2 GB/s

Rambus DRAM (RDRAM)

(Sta06 Fig 5.14)



- **Works with fast Rambus memory bus (800Mbps)**
  - Controller + RDRAM modules
  - Access time ~ 12 ns, transfer rate ~ 4.8 GB/s
- **Speed slows down with many memory modules**
  - Serially connected on Rambus channel
  - Not good for servers with 1 GB memory (for now!)

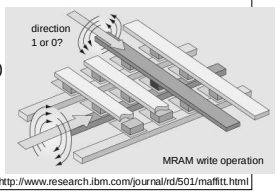
STI Cell processor

Flash memory

- **Based on transistors that are separated by a thin oxide layer**
  - Flash cell is analog, not digital storage: uses different charge levels to store 2 (or more) bits in each cell
- **Non-volatile, data remains with power off**
  - Electrical erasing in blocks = "flash"
  - Slow to write
  - Access time ~ 50 ns
- **Used as a solid state storage**
  - No moving parts
  - FlashBIOS in PC's, USB-memory
  - In phones, digital cameras, hand-held devices,....

MRAM

- **Magnetoresistive Random Access Memory (MRAM)**
  - Data stored with magnetic fields on two plates
  - Magnetic field directions determine bit value
- **Non-volatile, data remains with power off**
  - Fast to read/write
  - No upper limit for write counts (compare to Flash)
  - Access time comparable to DRAM
  - Almost as fast as SRAM
- **Future open**
  - Small market share now
  - Expensive now (2006: $25 4Mbit)
  - Still under development
  - May replace flash in a few years
  - May replace SRAM later on
  - May replace DRAM and become "universal memory"



MRAM write operation

http://www.research.ibm.com/journal/rd/501/maffitt.html

Kertauskysymyksiä

- **Muistihierarkia ja paikallisuus?**
- **Millä tavoin paikallisuutta huomiodaan välimuistiratkaisussa?**
- **Assosiatiivisen ja joukkoassosiatiivisen kuvauksen erot?**
- **Miksi käskyille oma välimuisti ja datalle oma?**